



PMCXB900UE

20 V, complementary N/P-channel Trench MOSFET

7 October 2013

Product data sheet

1. General description

Complementary N/P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Very low threshold voltage for portable applications: $V_{GS(th)} = 0.7\text{ V}$
- Leadless ultra small and ultra thin SMD plastic package: $1.1 \times 1.0 \times 0.37\text{ mm}$
- ElectroStatic Discharge (ESD) protection $> 1\text{ kV HBM}$

3. Applications

- Relay driver
- High-speed line driver
- Level shifter
- Power management in battery-driven portables

4. Quick reference data

Table 1. Quick reference data

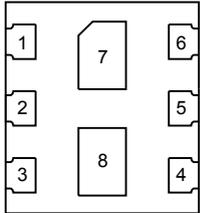
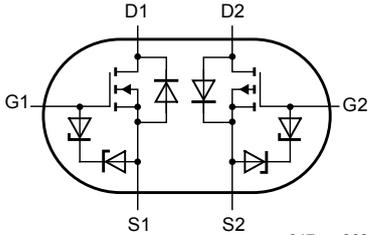
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
TR1 (N-channel), Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 600\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	-	470	620	m Ω
TR2 (P-channel), Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = -4.5\text{ V}; I_D = -500\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	-	1.02	1.4	Ω
TR1 (N-channel)						
V_{DS}	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$	-	-	20	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	600	mA
TR2 (P-channel)						
V_{DS}	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$	-	-	-20	V
I_D	drain current	$V_{GS} = -4.5\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	-500	mA



[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	 <p>Transparent top view DFN1010B-6 (SOT1216)</p>	 <p>017aaa262</p>
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1		
7	D1	drain TR1		
8	D2	drain TR2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMCXB900UE	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216

7. Marking

Table 4. Marking codes

Type number	Marking code
PMCXB900UE	10 00 00

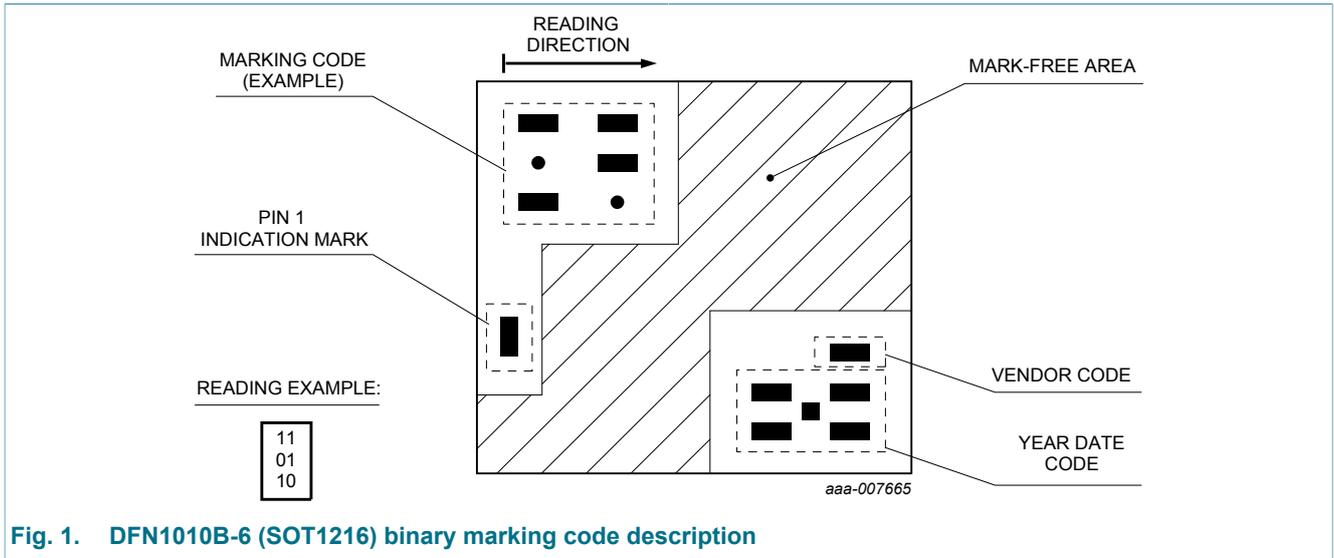


Fig. 1. DFN1010B-6 (SOT1216) binary marking code description

8. Limiting values

Table 5. Limiting values

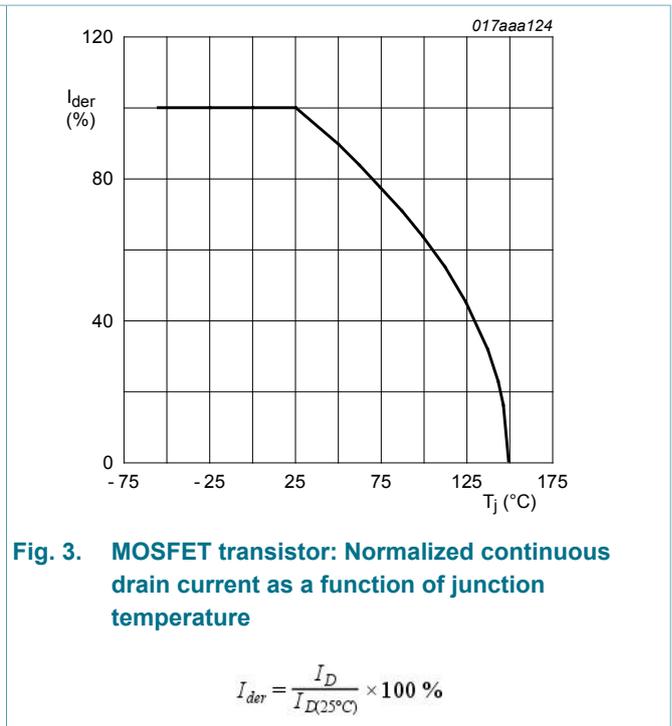
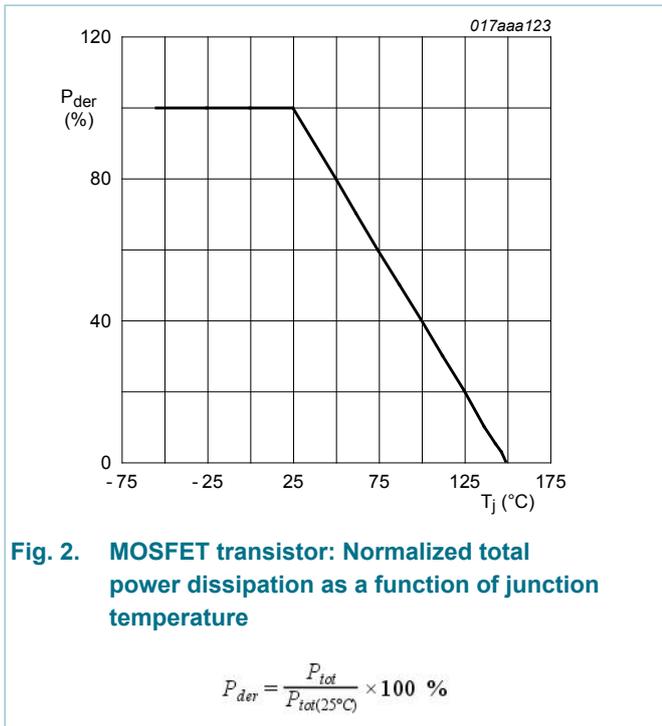
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
TR1 (N-channel)						
V_{DS}	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$		-	20	V
V_{GS}	gate-source voltage			-8	8	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	600	mA
		$V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ }^\circ\text{C}$	[1]	-	400	mA
I_{DM}	peak drain current	$T_{amb} = 25\text{ }^\circ\text{C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$		-	2.5	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^\circ\text{C}$	[2]	-	265	mW
			[1]	-	380	mW
		$T_{sp} = 25\text{ }^\circ\text{C}$		-	4025	mW
TR1 (N-channel), Source-drain diode						
I_S	source current	$T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	400	mA
TR2 (P-channel)						
V_{DS}	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$		-	-20	V
V_{GS}	gate-source voltage			-8	8	V

20 V, complementary N/P-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Max	Unit
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-500	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-300	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	-2	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	265	mW
			[1]	-	380	mW
		T _{sp} = 25 °C		-	4025	mW
TR2 (P-channel), Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	-350	mA
Per device						
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



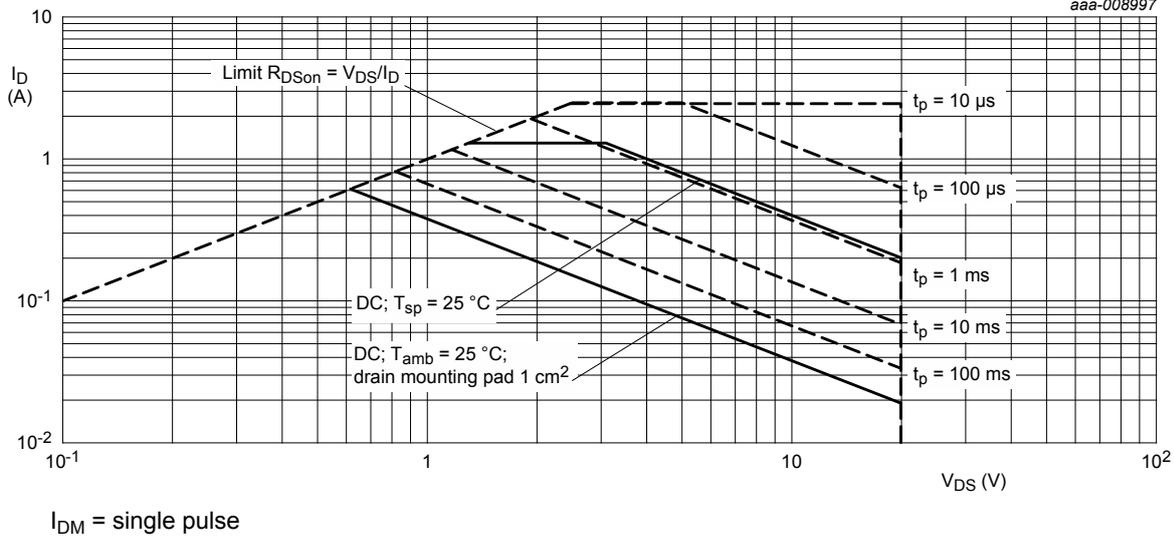


Fig. 4. TR1 (N-channel): safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

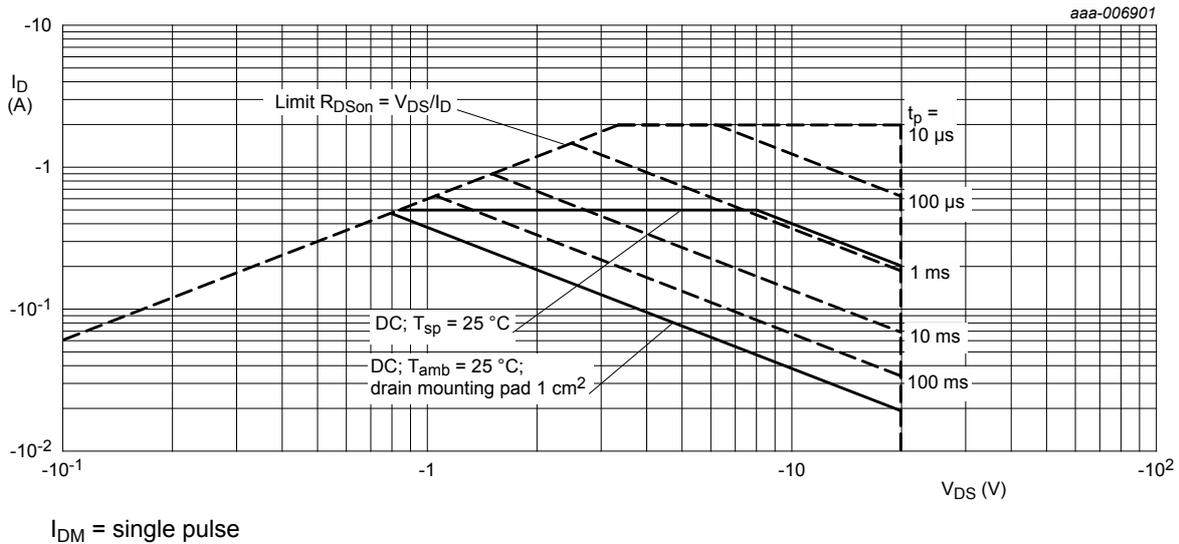


Fig. 5. TR2 (P-channel): safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

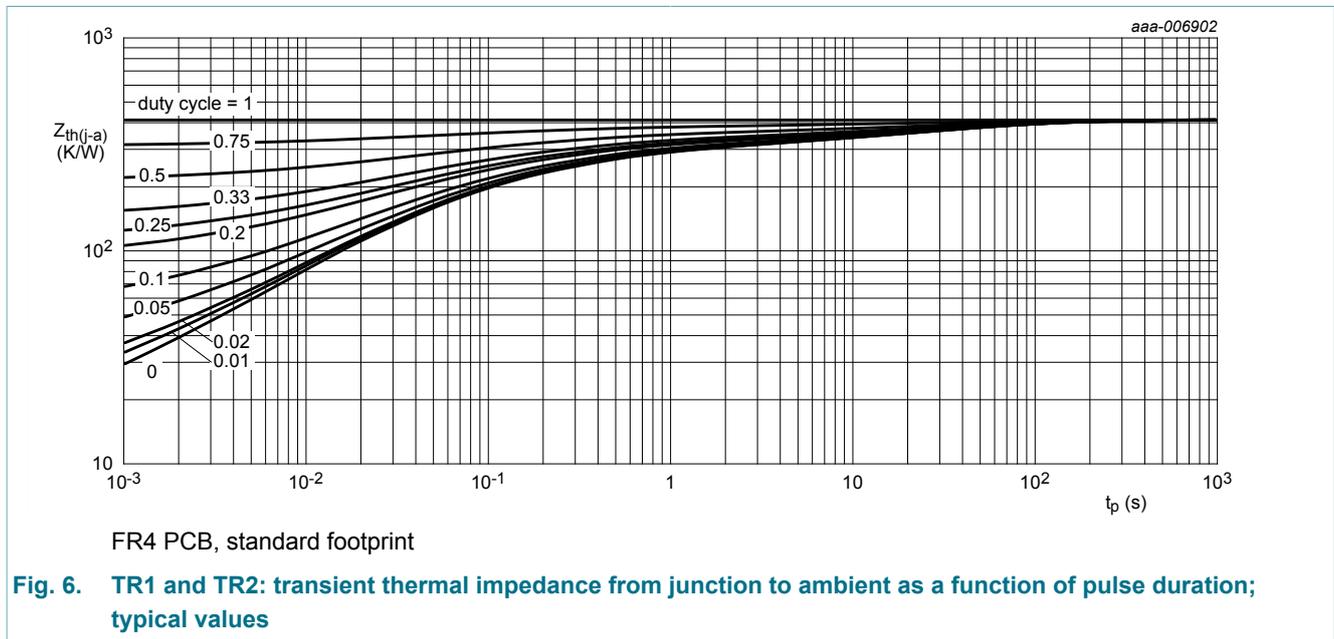
9. Thermal characteristics

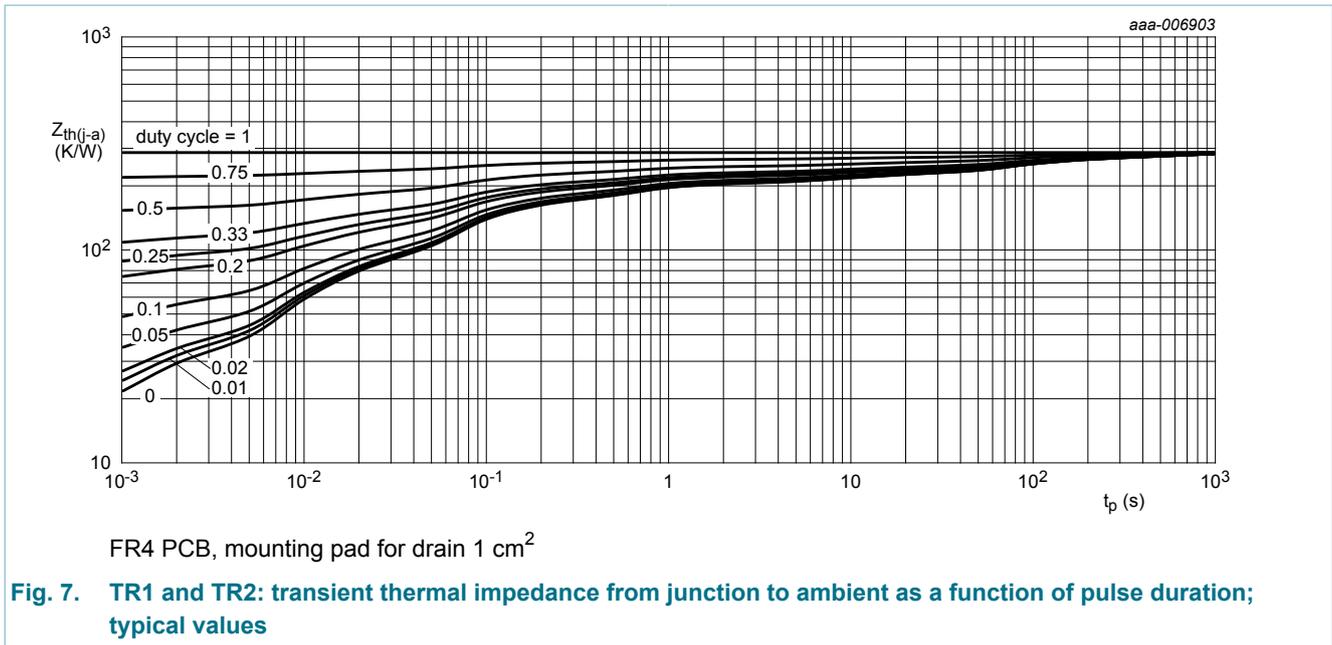
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
TR1 (N-channel)							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	410	475	K/W
			[2]	-	285	330	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	27	31	K/W
TR2 (P-channel)							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	410	475	K/W
			[2]	-	285	330	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	27	31	K/W

[1] Device mounted on an FR4 PCB, single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².





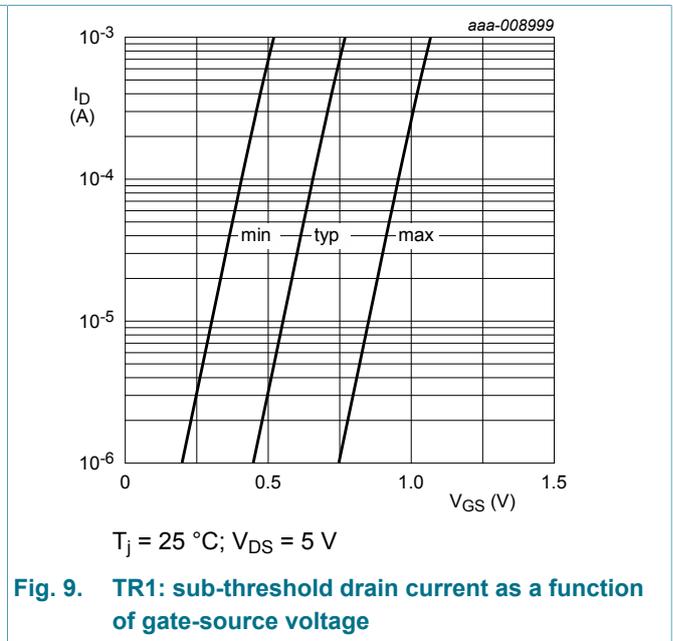
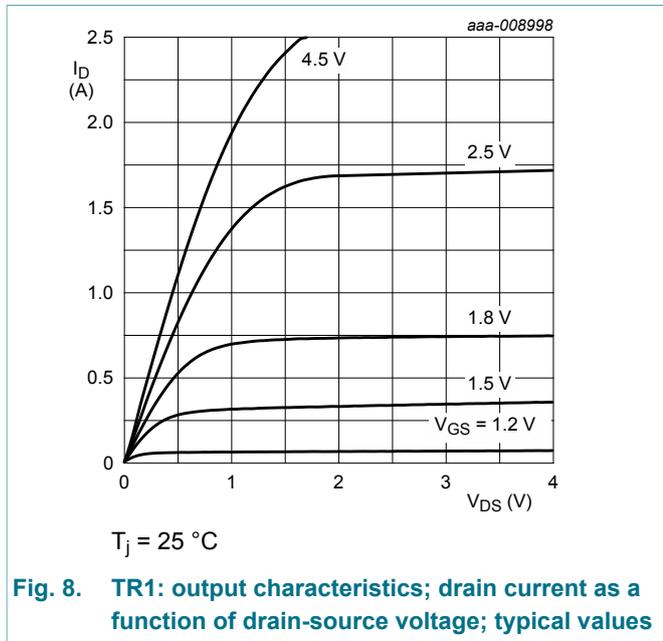
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
TR1 (N-channel), Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	0.45	0.7	0.95	V
I_{DSS}	drain leakage current	$V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	μA
I_{GSS}	gate leakage current	$V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	10	μA
		$V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	μA
		$V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-1	μA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 V; I_D = 600 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	470	620	m Ω
		$V_{GS} = 4.5 V; I_D = 600 \text{ mA}; T_j = 150 \text{ }^\circ C$	-	760	1000	m Ω
		$V_{GS} = 2.5 V; I_D = 500 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	620	850	m Ω
		$V_{GS} = 1.8 V; I_D = 100 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	845	1300	m Ω
		$V_{GS} = 1.5 V; I_D = 10 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	1125	3000	m Ω
		$V_{GS} = 1.2 V; I_D = 1 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	2210	-	m Ω
g_{fs}	transfer conductance	$V_{DS} = 5 V; I_D = 600 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	1	-	S

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
TR1 (N-channel), Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 10\text{ V}; I_D = 600\text{ mA}; V_{GS} = 4.5\text{ V};$ $T_j = 25\text{ }^\circ\text{C}$	-	0.4	0.7	nC
Q_{GS}	gate-source charge		-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C_{iss}	input capacitance	$V_{DS} = 10\text{ V}; f = 1\text{ MHz}; V_{GS} = 0\text{ V};$ $T_j = 25\text{ }^\circ\text{C}$	-	21.3	-	pF
C_{oss}	output capacitance		-	5.4	-	pF
C_{rss}	reverse transfer capacitance		-	4.2	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 10\text{ V}; I_D = 600\text{ mA}; V_{GS} = 4.5\text{ V};$ $R_{G(ext)} = 6\text{ }^\Omega; T_j = 25\text{ }^\circ\text{C}$	-	5.6	-	ns
t_r	rise time		-	9.2	-	ns
$t_{d(off)}$	turn-off delay time		-	19	-	ns
t_f	fall time		-	51	-	ns
TR1 (N-channel), Source-drain diode characteristics						
V_{SD}	source-drain voltage	$I_S = 360\text{ mA}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	0.8	1.2	V
TR2 (P-channel), Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250\text{ }^\mu\text{A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250\text{ }^\mu\text{A}; V_{DS} = V_{GS}; T_j = 25\text{ }^\circ\text{C}$	-0.45	-0.7	-0.95	V
I_{DSS}	drain leakage current	$V_{DS} = -20\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	-1	μA
I_{GSS}	gate leakage current	$V_{GS} = 8\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	10	μA
		$V_{GS} = -8\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	-10	μA
		$V_{GS} = 4.5\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	1	μA
		$V_{GS} = -4.5\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	-1	μA
R_{DSon}	drain-source on-state resistance	$V_{GS} = -4.5\text{ V}; I_D = -500\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	-	1.02	1.4	Ω
		$V_{GS} = -4.5\text{ V}; I_D = -500\text{ mA}; T_j = 150\text{ }^\circ\text{C}$	-	1.54	2.1	Ω
		$V_{GS} = -2.5\text{ V}; I_D = -200\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	-	1.27	2.2	Ω
		$V_{GS} = -1.8\text{ V}; I_D = -40\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	-	1.7	3.3	Ω
		$V_{GS} = -1.5\text{ V}; I_D = -10\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	-	2.3	5	Ω
		$V_{GS} = -1.2\text{ V}; I_D = -1\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	-	3.5	-	Ω
g_{fs}	transfer conductance	$V_{DS} = -10\text{ V}; I_D = -500\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	-	480	-	mS
TR2 (P-channel), Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = -10\text{ V}; I_D = -450\text{ mA};$ $V_{GS} = -4.5\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	1.19	2.1	nC
Q_{GS}	gate-source charge		-	0.17	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{iss}	input capacitance	$V_{DS} = -10\text{ V}; f = 1\text{ MHz}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	43	-	pF
C_{oss}	output capacitance		-	14	-	pF
C_{rss}	reverse transfer capacitance		-	8	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = -10\text{ V}; I_D = -450\text{ mA}; V_{GS} = -4.5\text{ V}; R_{G(ext)} = 6\text{ }\Omega; T_j = 25\text{ }^\circ\text{C}$	-	2.3	-	ns
t_r	rise time		-	5	-	ns
$t_{d(off)}$	turn-off delay time		-	13.5	-	ns
t_f	fall time		-	6	-	ns
TR2 (P-channel), Source-drain diode characteristics						
V_{SD}	source-drain voltage	$I_S = -115\text{ mA}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-0.7	-1.2	V



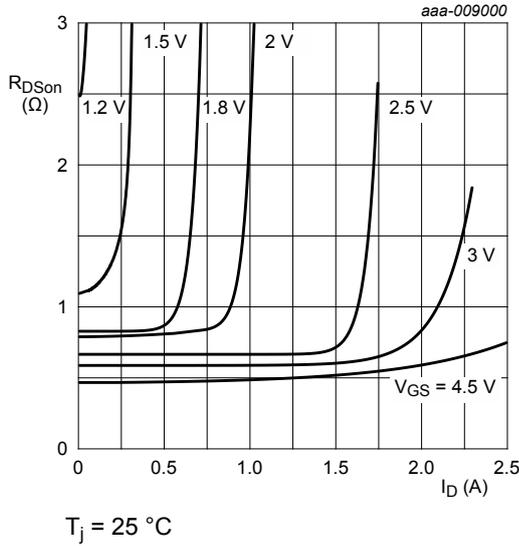


Fig. 10. TR1: drain-source on-state resistance as a function of drain current; typical values

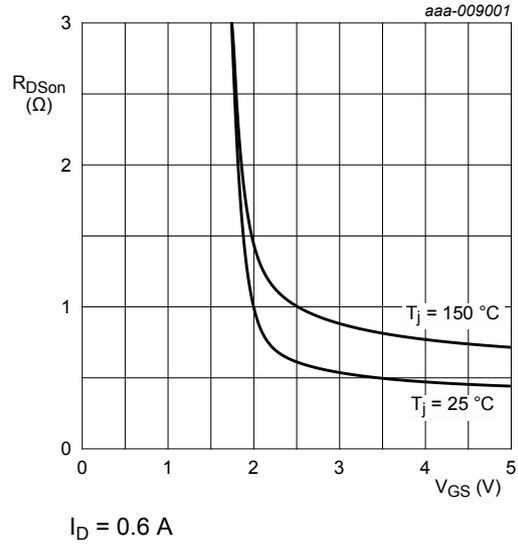


Fig. 11. TR1: drain-source on-state resistance as a function of gate-source voltage; typical values

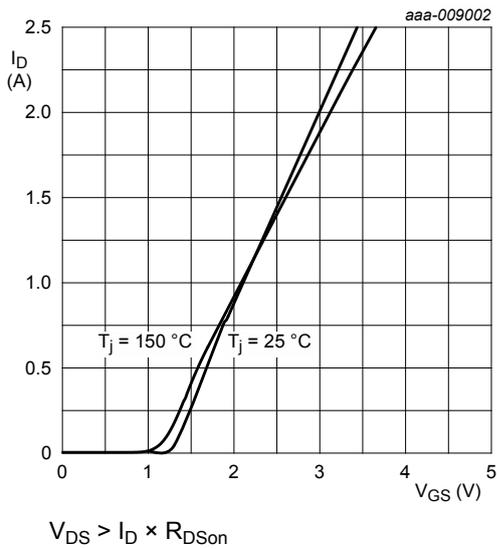


Fig. 12. TR1: transfer characteristics; drain current as a function of gate-source voltage; typical values

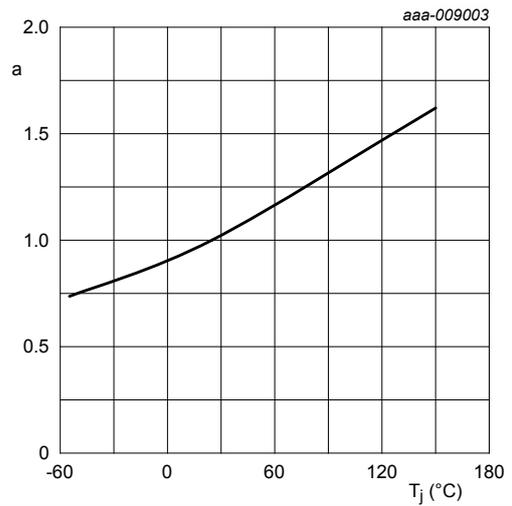
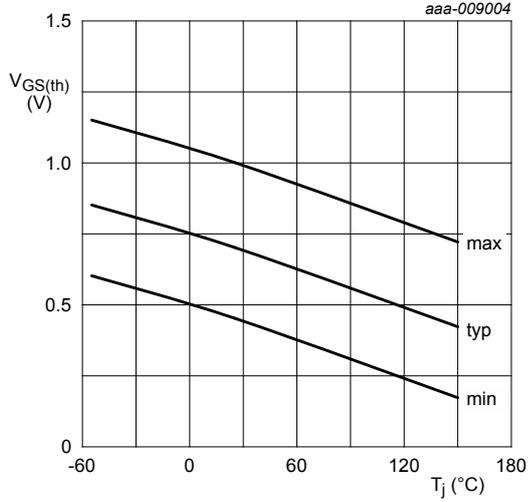


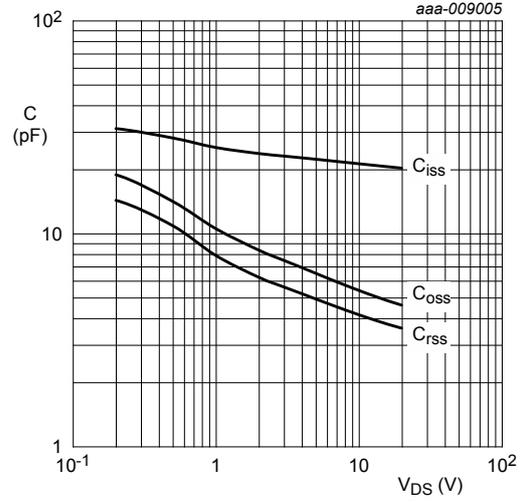
Fig. 13. TR1: normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$



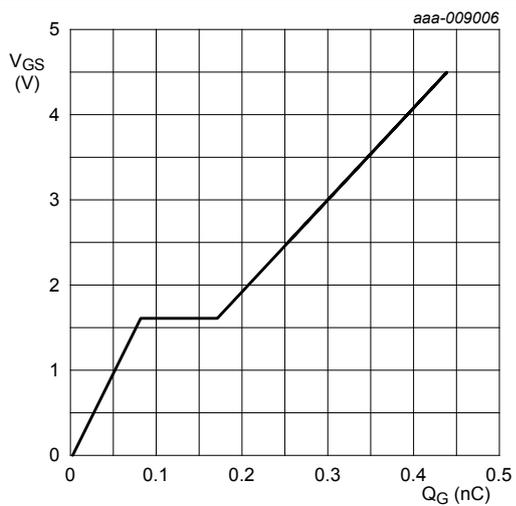
$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

Fig. 14. TR1: gate-source threshold voltage as a function of junction temperature



$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

Fig. 15. TR1: input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 0.6 \text{ A}; V_{DS} = 10 \text{ V}; T_{amb} = 25 \text{ °C}$

Fig. 16. TR1: gate-source voltage as a function of gate charge; typical values

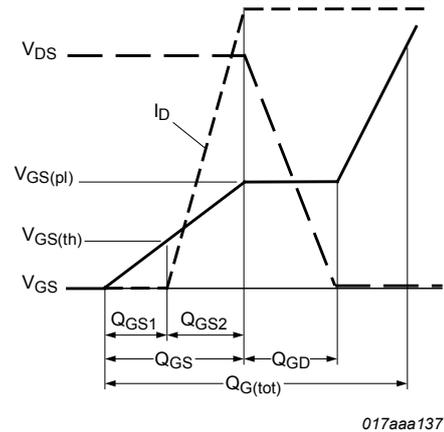


Fig. 17. Gate charge waveform definitions

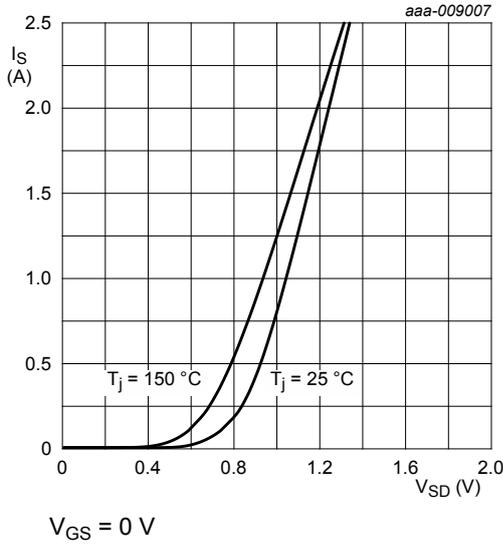


Fig. 18. TR1: source current as a function of source-drain voltage; typical values

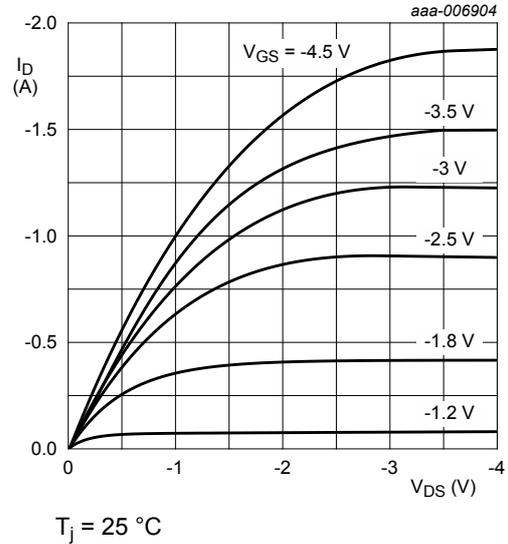


Fig. 19. TR2: output characteristics; drain current as a function of drain-source voltage; typical values

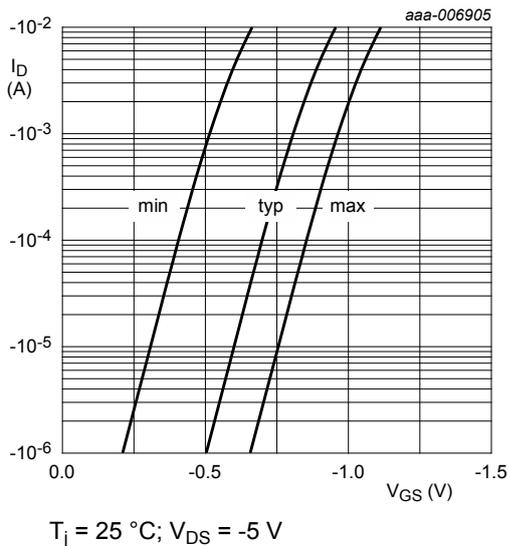


Fig. 20. TR2: sub-threshold drain current as a function of gate-source voltage

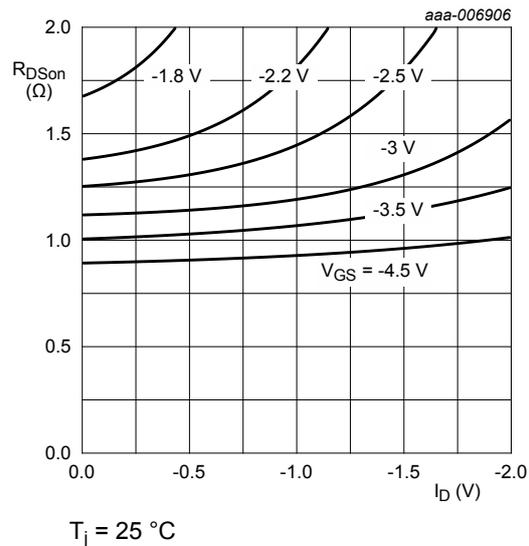


Fig. 21. TR2: drain-source on-state resistance as a function of drain current; typical values

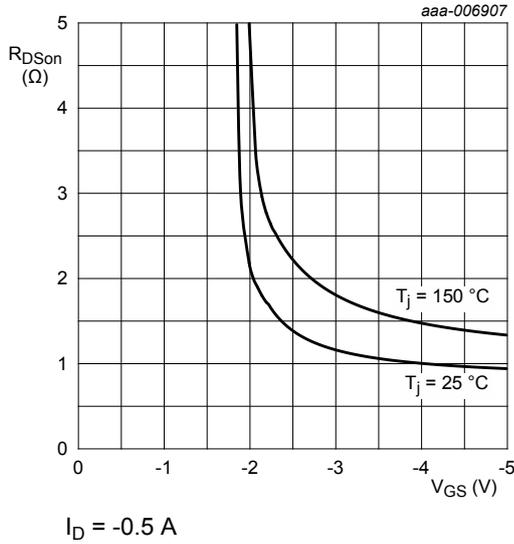


Fig. 22. TR2: drain-source on-state resistance as a function of gate-source voltage; typical values

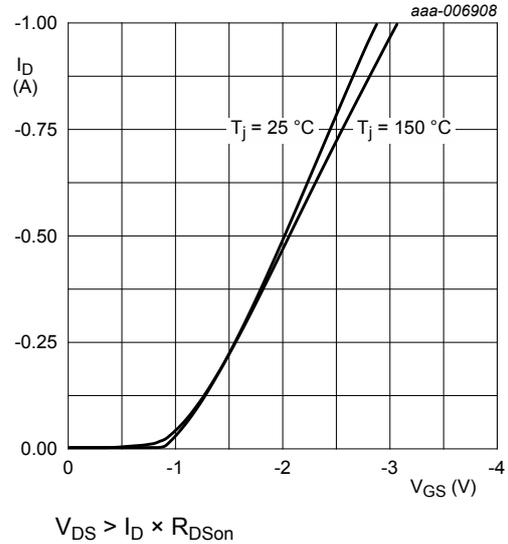


Fig. 23. TR2: transfer characteristics; drain current as a function of gate-source voltage; typical values

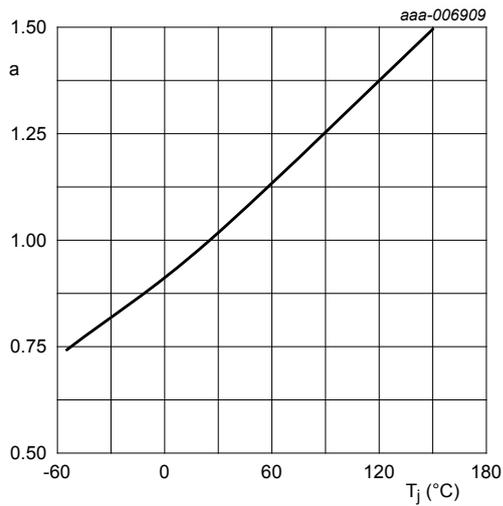


Fig. 24. TR2: normalized drain-source on-state resistance as a function of junction temperature; typical values

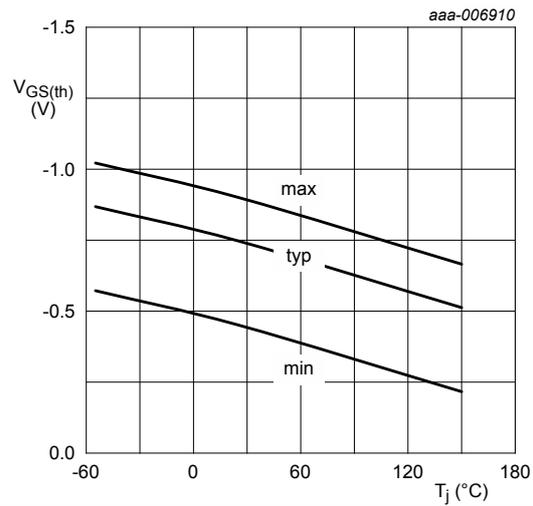
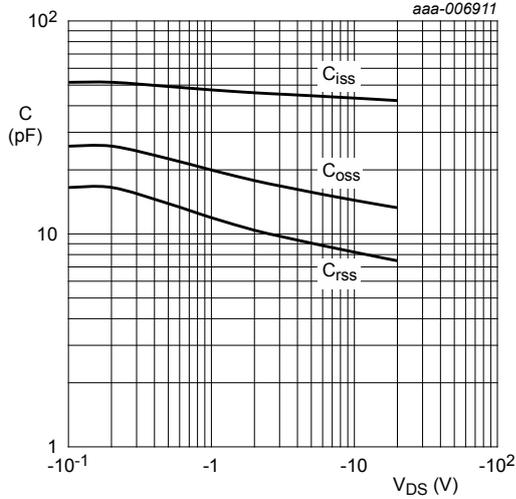
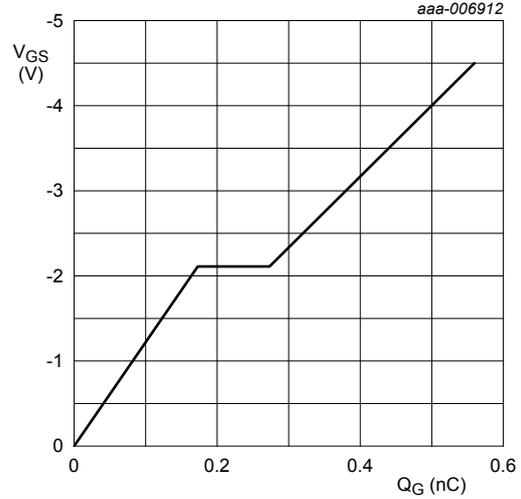


Fig. 25. TR2: gate-source threshold voltage as a function of junction temperature



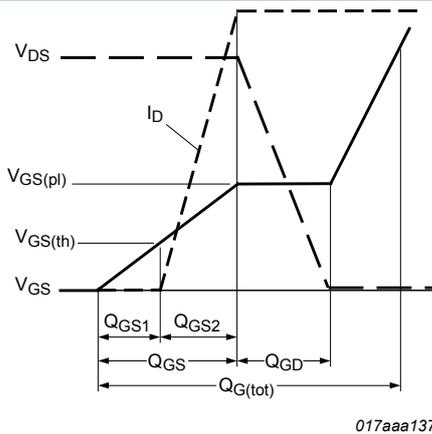
f = 1 MHz; V_{GS} = 0 V

Fig. 26. TR2: input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



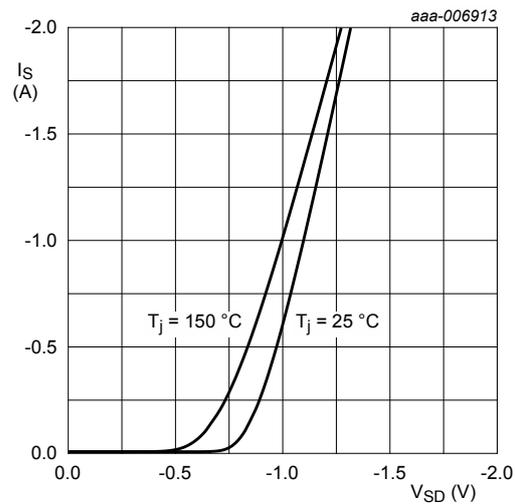
I_D = -0.45 A; V_{DS} = -10 V; T_{amb} = 25 °C

Fig. 27. TR2: gate-source voltage as a function of gate charge; typical values



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Fig. 28. Gate charge waveform definitions



V_{GS} = 0 V

Fig. 29. TR2: source current as a function of source-drain voltage; typical values

11. Test information

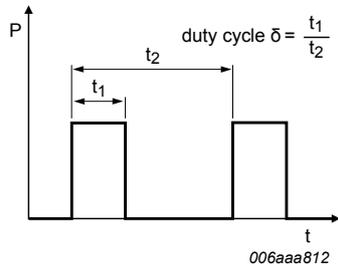


Fig. 30. Duty cycle definition

12. Package outline

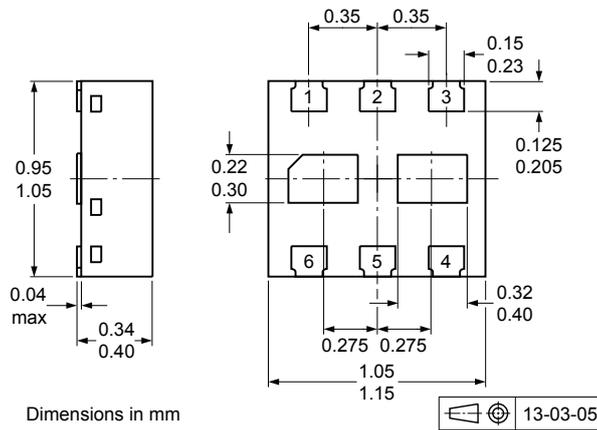


Fig. 31. Package outline DFN1010B-6 (SOT1216)

13. Soldering

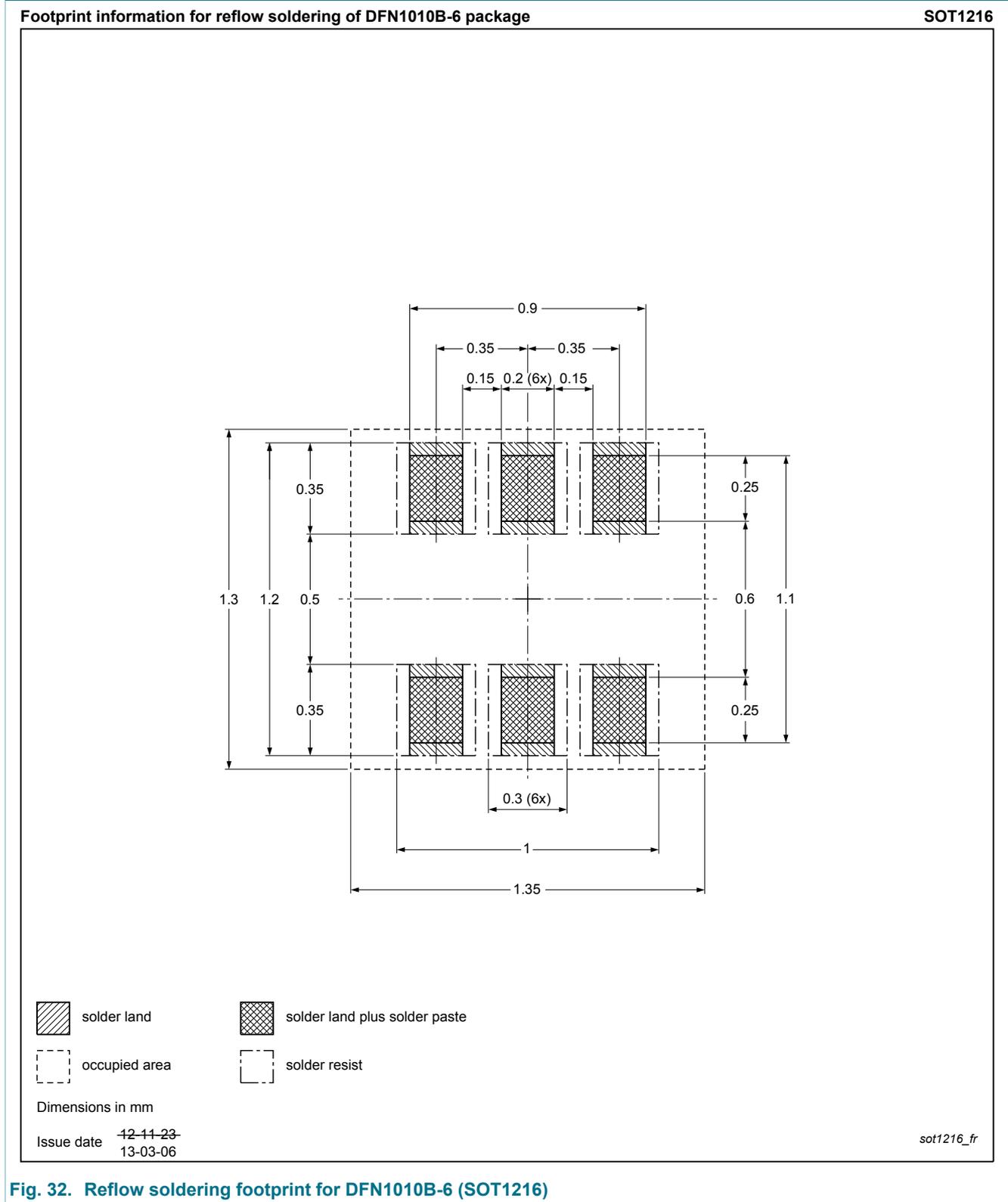


Fig. 32. Reflow soldering footprint for DFN1010B-6 (SOT1216)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMCXB900UE v.1	20131007	Product data sheet	-	-

15. Legal information

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Document status [1][2]	Product status [3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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